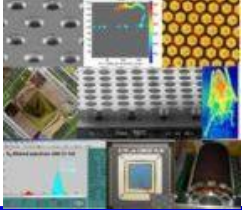


DISCHARGE STUDIES BY THE TRIESTE GROUP

S. Dalla Torre, S. Dasgupta, G. Hamar, S.
Levorato, A. Mucchietto, F. Pereira, C. Santos,
F. Tessarotto

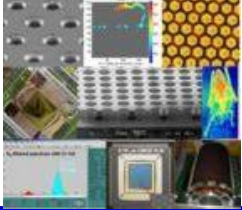


OUTLOOK

A COLLECTION OF DATA ACCUMULATED OVER YEARS

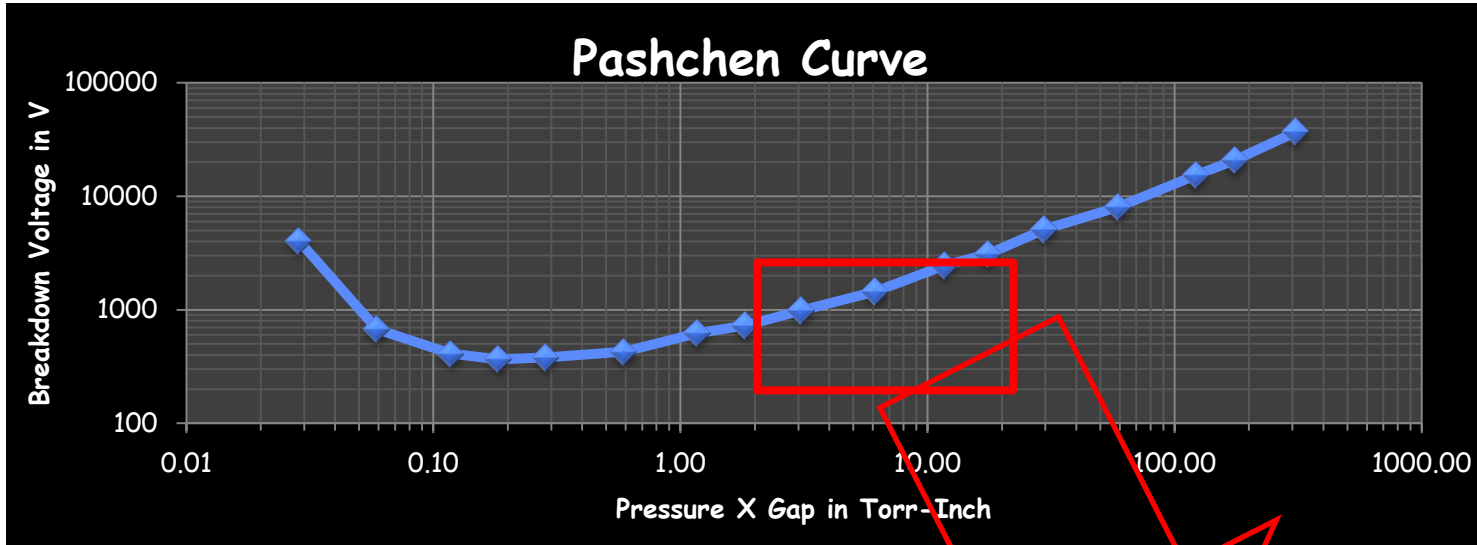
- **DISCHARGES IN THGEMs**
 - The PASCHEN TEST tool
 - PASCHEN test vs detector discharges
 - The role of the PCB quality in discharge rates
 - The discharge cross-talk of the sectors of a large THGEM

- **DISCHARGES IN RESISTIVE MICROMEAS**
 - Space, time correlations
 - Inefficiencies at microscopic time-scale level



THGEM

A conceptual tool: THE PASCHEN CURVE (EMPIRICAL)



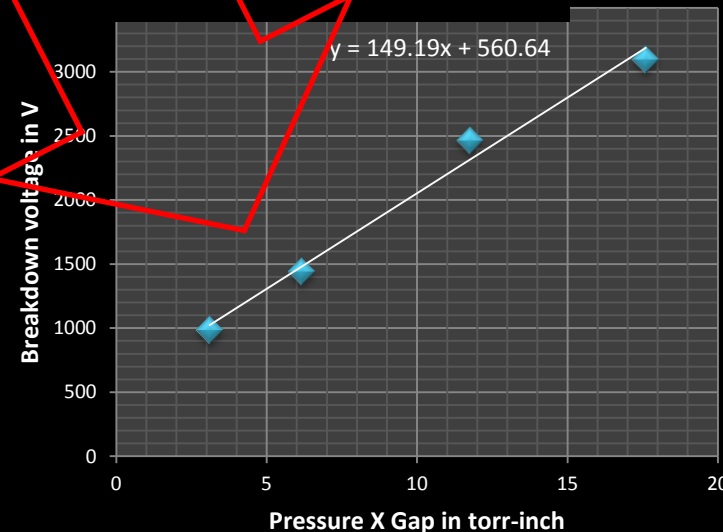
The breakdown V_{bd} depends on

- P
- d (electrode distance)
- the specific gas

$$d = 0.4 \text{ mm} \rightarrow V_{bd} = 2270 \text{ V}$$

$$\Delta d = 20 \text{ } \mu\text{m} \rightarrow \Delta V_{bd} = 100 \text{ V}$$

$$\Delta P = 20 \text{ mbar} \rightarrow \Delta V_{bd} = 35 \text{ V}$$

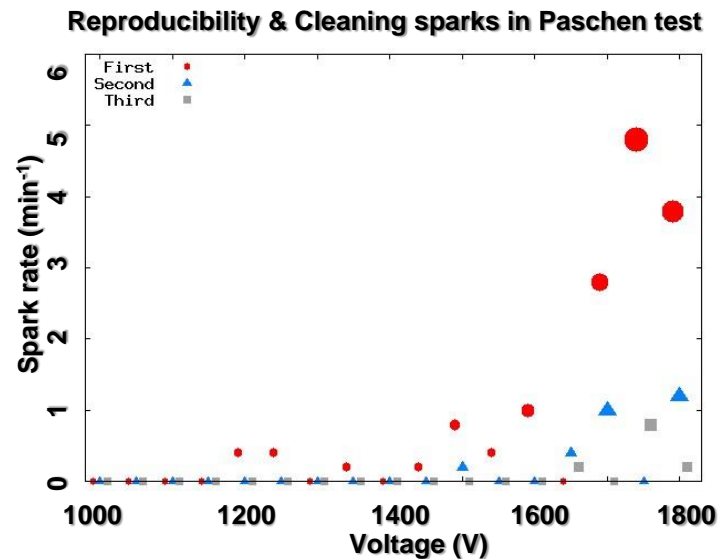


(air)
For our case
pressure ~ 970 mbar
 $= 727.56$ torr, gap \sim
 0.4 mm $= 0.01575$ m.
So Pressure X Gap =
11.45 torr-inch

THGEM DISCHARGE STUDIES 1/3

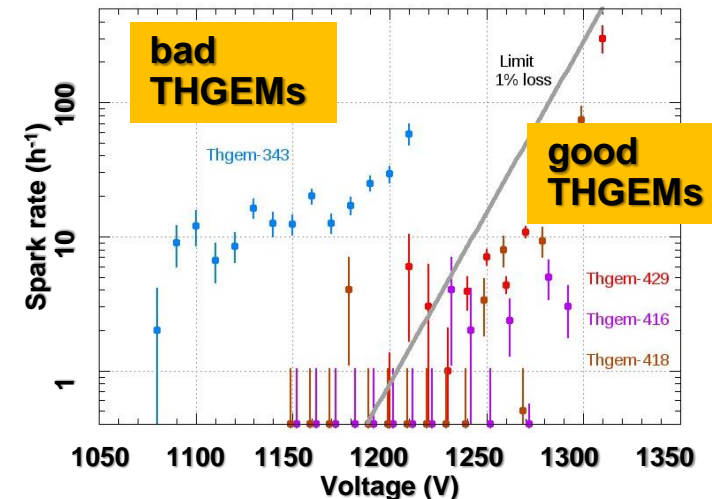
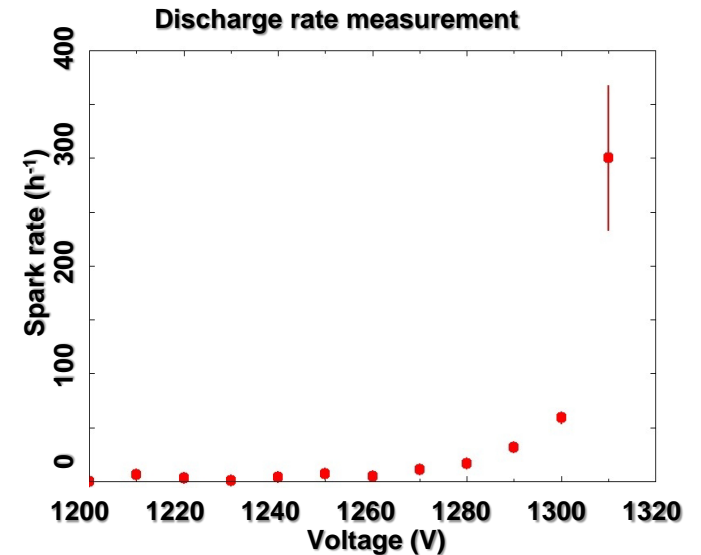
■ PASCHEN LIMIT

- Paschen measurements in N_2 (expected Paschen limit at $\sim 2250V$)
 - The measured limit is set at the HV where discharge rates $\approx 1/\text{min}$
 - $30 \times 60 \text{ cm}^2$ THGEMs:
 - thickness 04. mm, pitch: 0.8 mm, hole diameter 0.4 mm
 - 325 k holes !!!
 - Note the “cleaning” discharges (at first test)
 - Second and third test: reproducibility

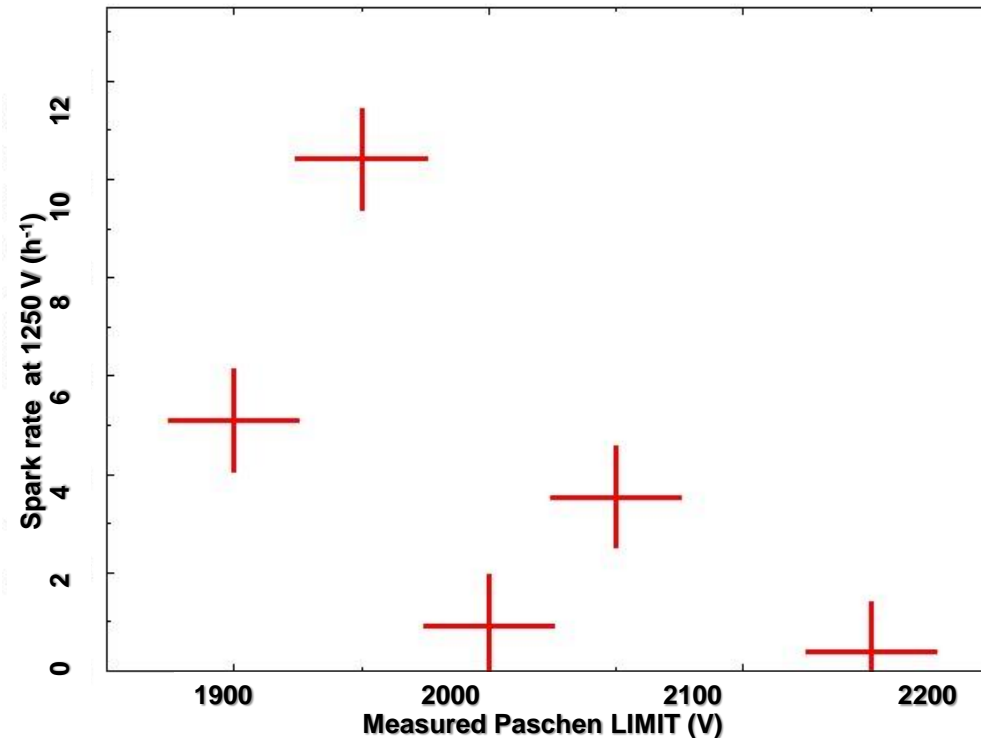


THGEM DISCHARGE STUDIES 2/3

- **DISCHARGE RATES** in single layer THGEM
 - Discharge rates measured in Ar : CO₂ = 70 : 30
- Which operation voltage (i.e. which gain)?
 - Gain (single layer) 20 → voltage 1125 V
- Tolerable discharge voltage ?
 - ARBITRARY fixed at 1% DEAD TIME for a total surface of 3 m²
 - Recovery time after a trip : 1 min
 - 1 trip/d for a 30x 60 cm² THGEM
 - Non directly measurable:
EXTRAPOLATION down to 1125 V

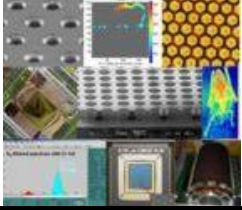


- **Correlation of PASCHEN LIMIT vs SPARK RATES**
 - Each point in the plot is a 30 x 60 cm² THGEM



- The simple PASCHEN test is a valid tool for THGEM QC
- Large surfaces with very low dead time rate can be instrumented

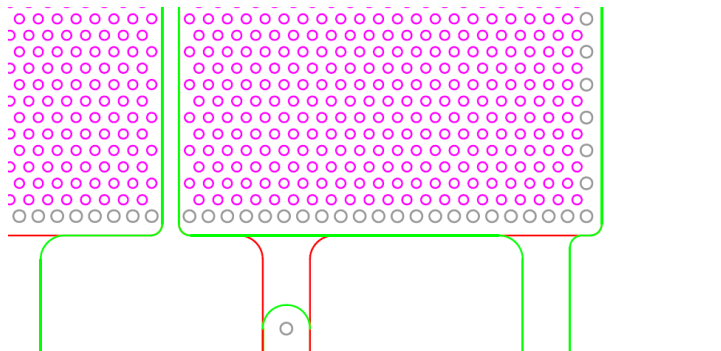
THGEM LAYOUT & DISCHARGES



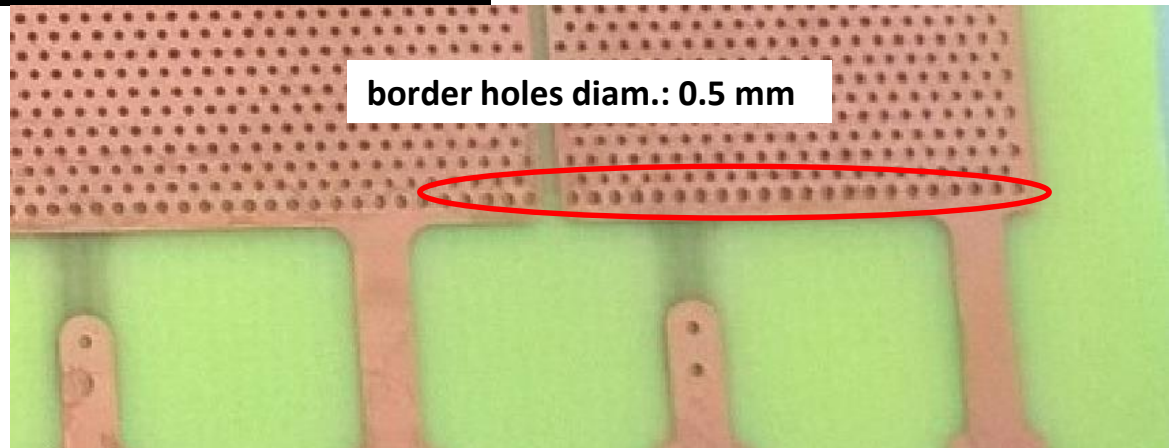
Thickness: 0.4 mm, hole diameter: 0.4 mm, pitch: 0.8 mm

12 sectors on both top and bottom, 0.7 mm separation

24 fixation points to guarantee THGEMs flatness



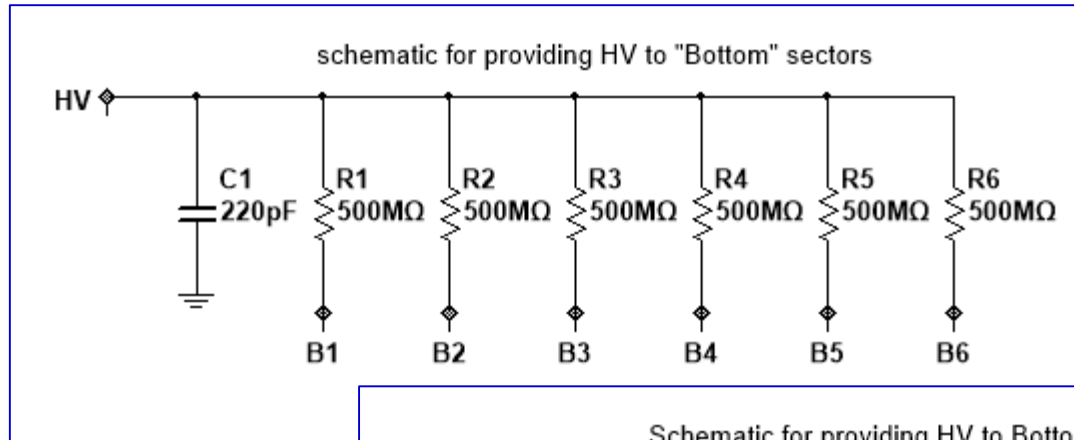
border holes diam.: 0.5 mm



DISCHARGE PROPAGATION WITHIN A THGEM

Discharge propagation from one sector to others (also non adjacent ones!)
→ HV distribution suspected, in particular to THGEM bottom

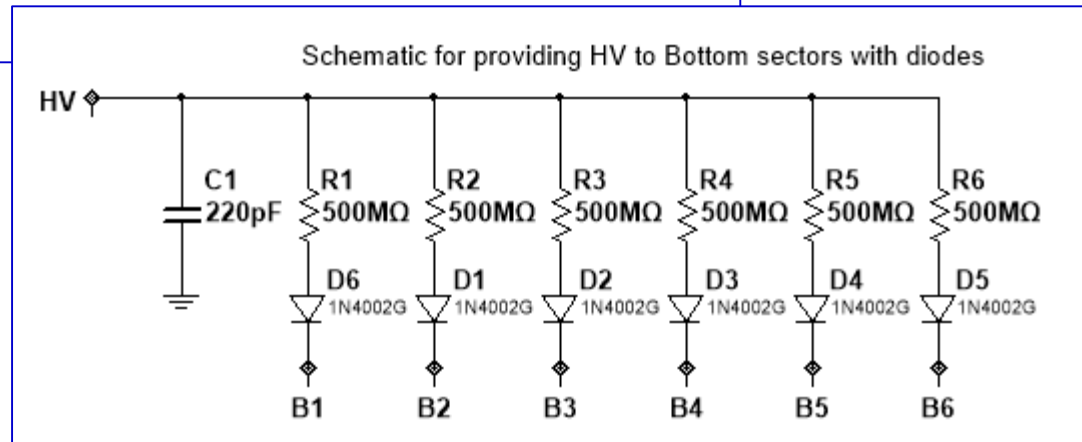
INITIALLY:



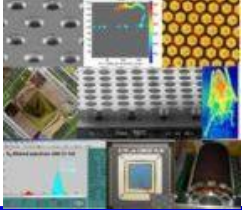
THEN:

Cross-talk is eliminated !

Analogous scheme also
for the top



Diode: VS-20ETS High Voltage, Input Rectifier Diode



MICROME GAS

RESISTIVE MM BY DISCRETE ELEMENTS

Resistive elements:

a decision made because we have to be on the floor in 2016

Our MM:

- Standard bulk, built at CERN
- Gap: 128 μm
- Pad geometry: squared, pitch 8 mm, clearance 0.5 mm
- Gas mixture for the tests:

Ar : CO₂ = 70 : 30

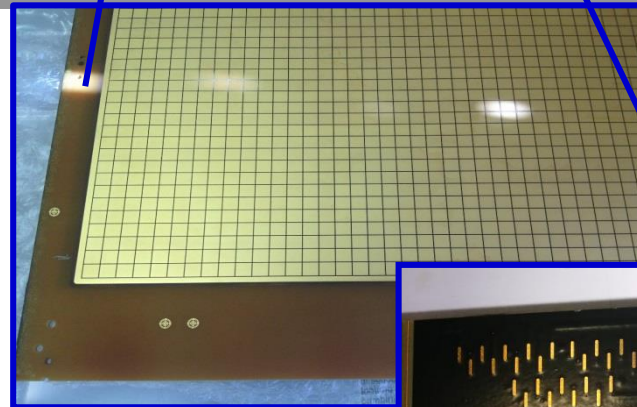
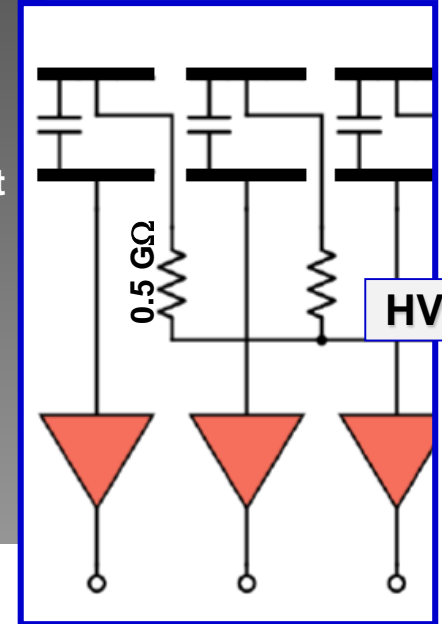
Single pad

HV is applied here through a resistor (mesh @ ground)

0.15 mm fiberglass

Signal read-out from this pad

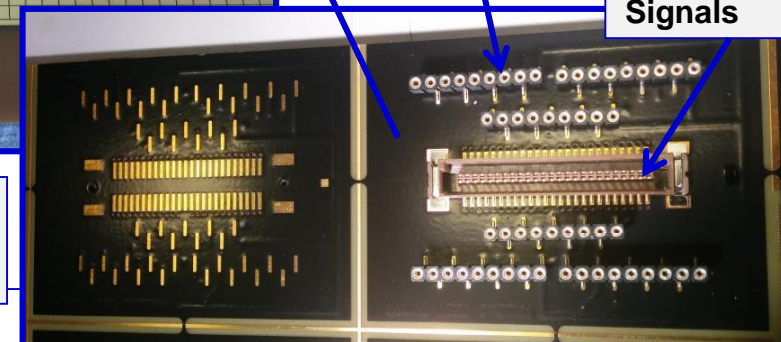
PCB



Connections for groups of 48 pads

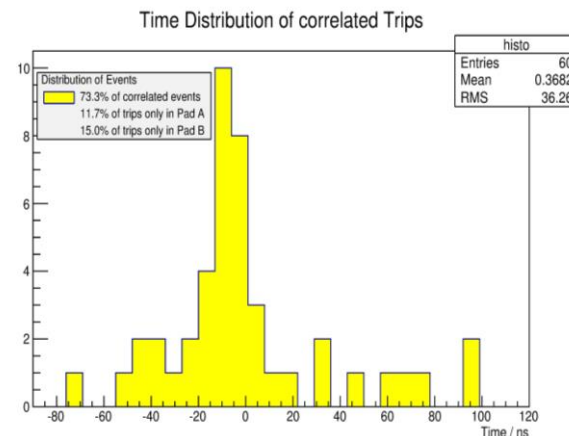
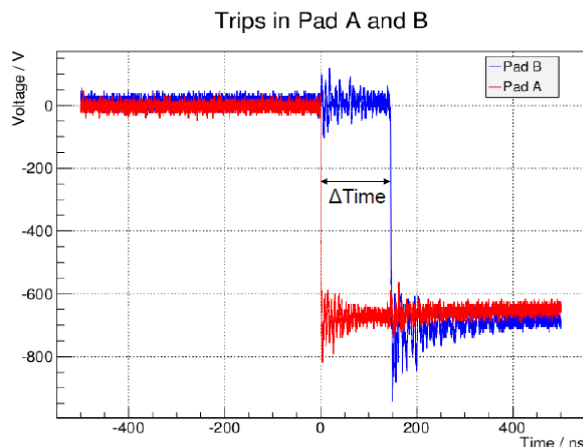
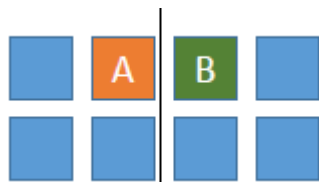
Resistor arrays

Signals



NO TRIP CROSS-TALK VIA PCB !

- Two adjacent pads kept at anomalous high voltage (720 V) to enhance trip frequency ($\sim 0.1-0.2$ Hz)

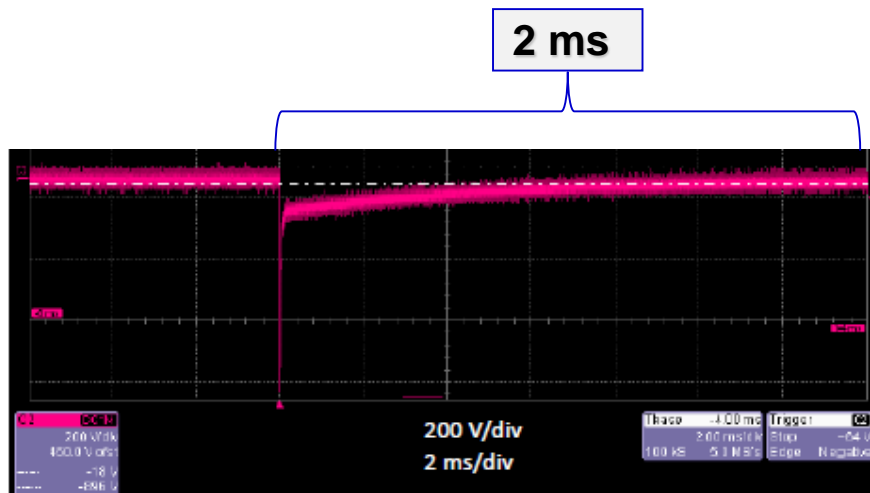
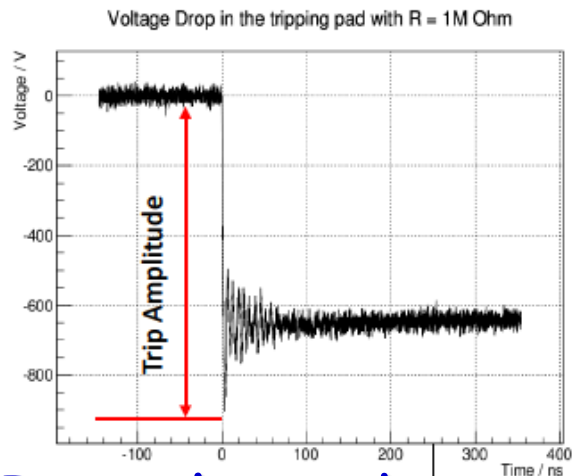


- One of the 2 pads at standard voltage : no trip observed

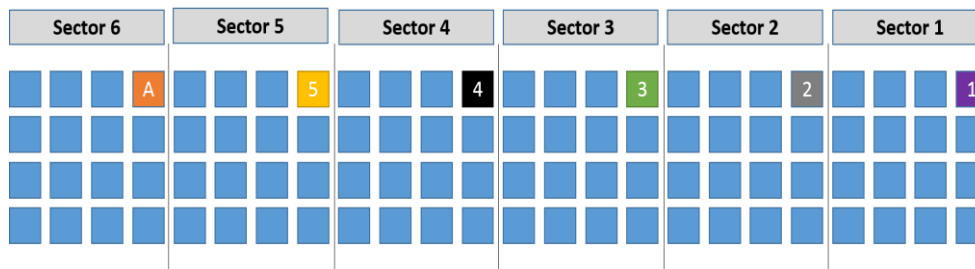
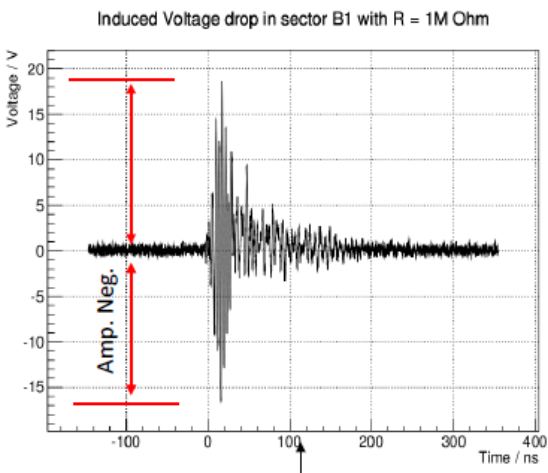
Couple d position	V(A)	V(B)	% correlated events	% only in A	% only in B
AB	720	720	73.3	11.7	15
AB	735	720	90	8.3	1.7
AB	720	735	70.5	1.6	27.9
AB	730	600	0	100	0
AB	600	730	0	0.0	100

TRIP PICTURES

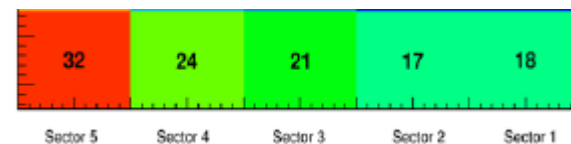
Discharge in Pad A (720 V)



In another pad:

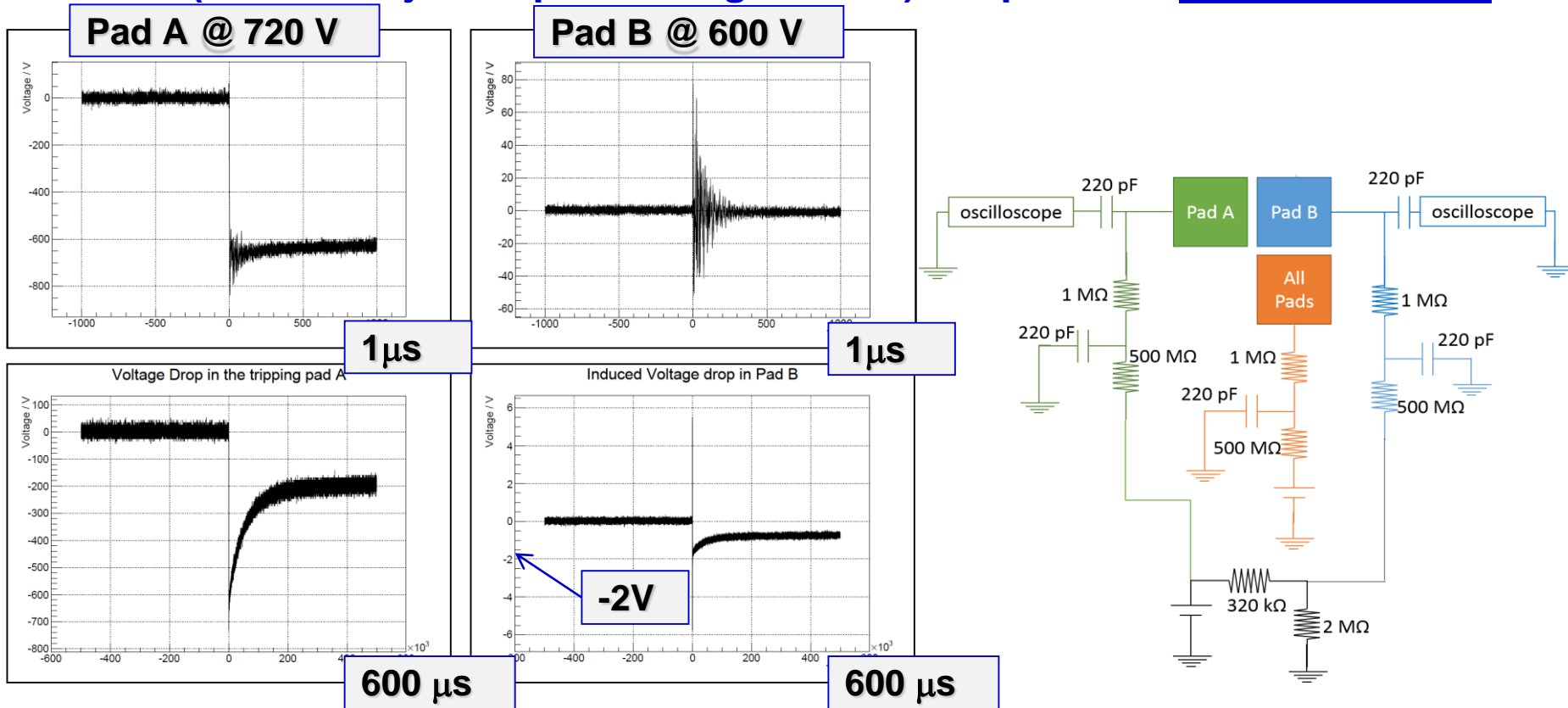


the amplitude decreases with the distance



RESPONSE OF THE NON-TRIPPING PAD

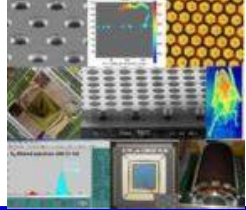
Pads A & B (the two adjacent pads being studied) are powered by the same PS



The HV of the non tripping pad is very limited affected:

2V drop \rightarrow \sim 4% drop in G

R \sim 0.5 G Ω is preserving the non-tripping pads efficient all the time !



I AM THE ONLY ONE
FROM TRIESTE ATTENDING
THE MEETING
BECAUSE ...

THE FIRST LARGE-SIZE MPGD-BASED SINGLE PHOTON DETECTORS ARE COMING !

